Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Enhanced power dissipation capability of 1240 mW

3. Applications

- · Relay driver
- · High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-4.7	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3.7 A; T_j = 25 °C		-	50	62	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate	©	G T
4	S	source		\$ 017aaa257
5	D	drain		
6	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
PMN52XP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457				

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN52XP	H3

20 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-4.7	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.7	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-15	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	530	mW
			[1]	-	1.24	W
		T _{sp} = 25 °C		-	4.46	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		'	'		
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.2	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

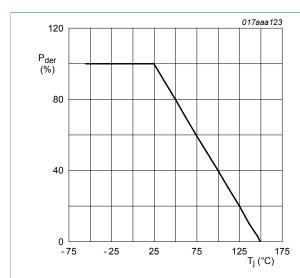


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

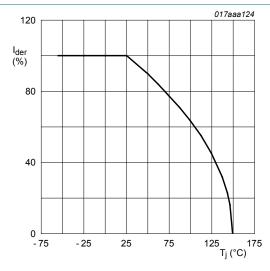


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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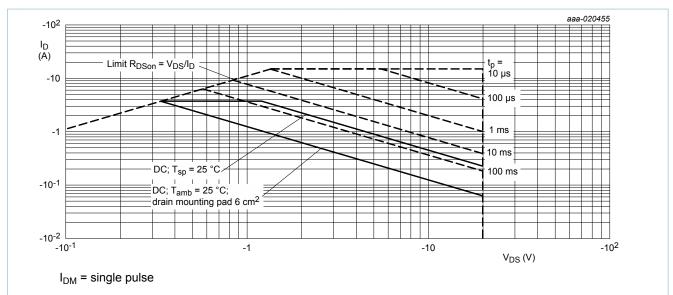


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

4/16

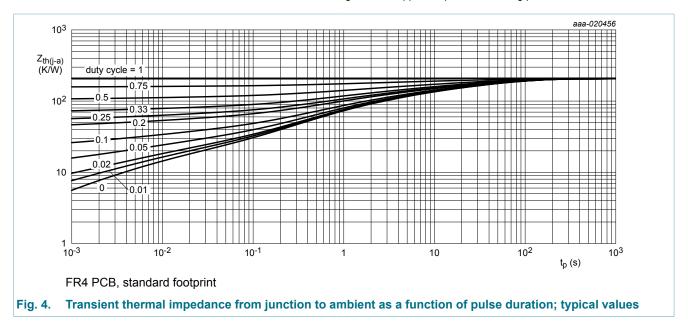
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9. Thermal characteristics

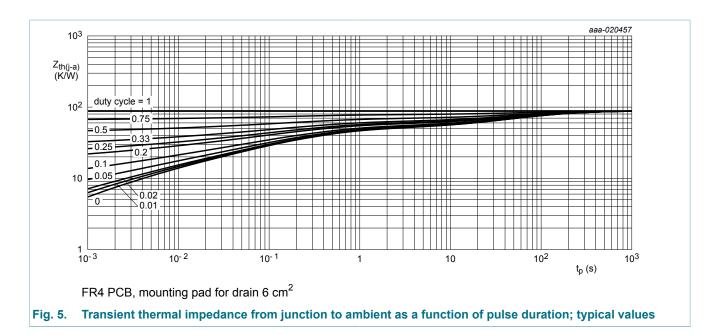
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	205	235	K/W
	from junction to ambient		<u>[2]</u>	-	88	101	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	55	63	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	24	28	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, P-channel Trench MOSFET



20 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mii	1 Тур	Max	Unit
Static char	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20) -	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.	47 -0.65	-0.9	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -3.7 A; T_j = 25 °C	-	50	62	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -3.7 A; T_j = 150 °C	-	73	91	mΩ
		V_{GS} = -2.5 V; I_D = -3.2 A; T_j = 25 °C	-	64	84	mΩ
		V _{GS} = -1.8 V; I _D = -1 A; T _j = 25 °C	-	88	125	mΩ
		V_{GS} = -1.5 V; I_D = -0.1 A; T_j = 25 °C	-	120	255	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -2 A; T_j = 25 °C	-	9	-	S
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -3.7 A; V_{GS} = -4.5 V;	-	8.5	12	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.1	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	763	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	68	-	pF
C _{rss}	reverse transfer capacitance		-	58	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -3.7 A; V_{GS} = -4.5 V;	-	5.1	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	4.3	-	ns
t _{d(off)}	turn-off delay time		-	141	-	ns
t _f	fall time		-	62	-	ns
Source-dra	ain diode	1	1	1	1	
V _{SD}	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V

7/16

20 V, P-channel Trench MOSFET

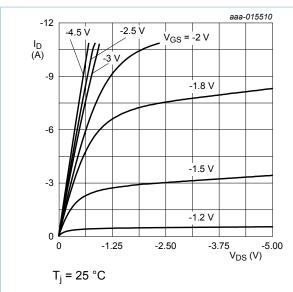


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

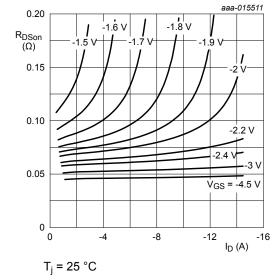


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

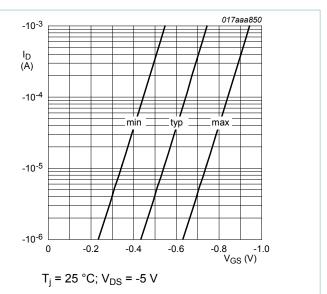


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

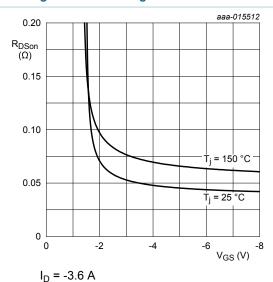


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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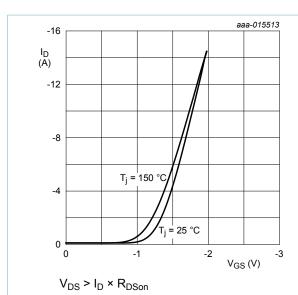


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

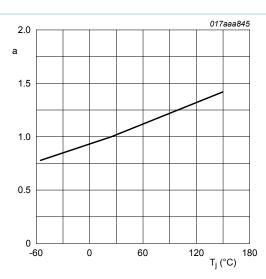


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

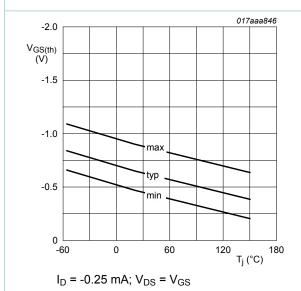


Fig. 12. Gate-source threshold voltage as a function of junction temperature

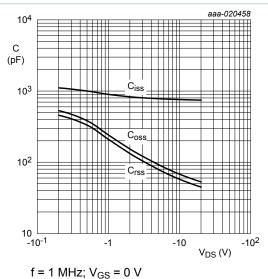


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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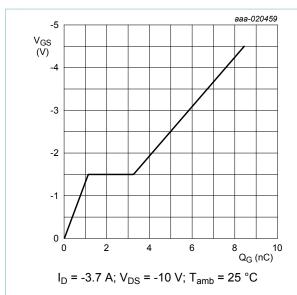


Fig. 14. Gate-source voltage as a function of gate charge; typical values

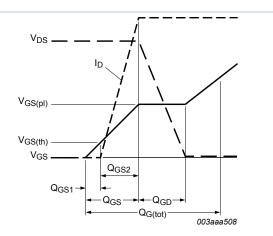


Fig. 15. MOSFET transistor: Gate charge waveform definitions

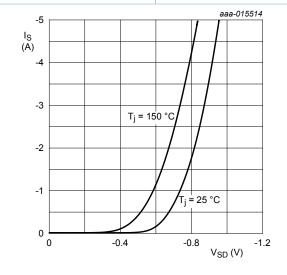
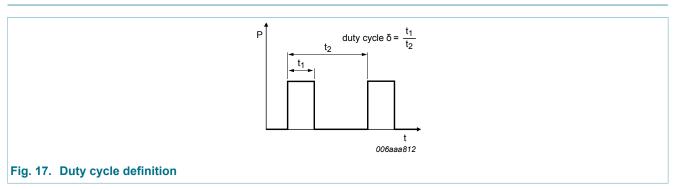


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



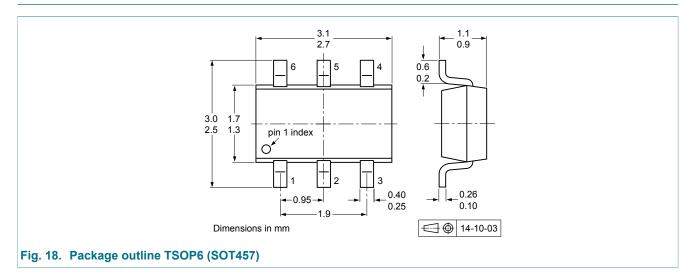
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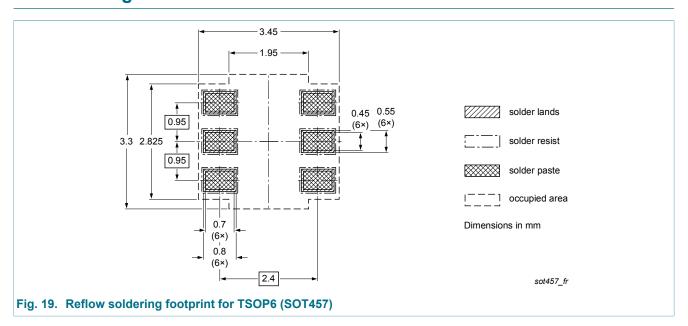
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20 V, P-channel Trench MOSFET

12. Package outline

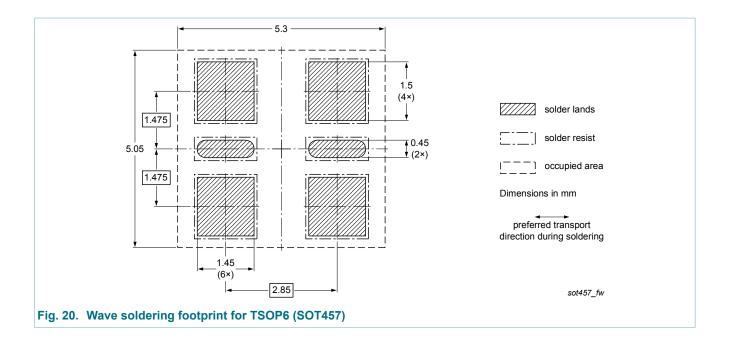


13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN52XP v.1	20160129	Product data sheet	-	-

20 V, P-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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20 V, P-channel Trench MOSFET

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20 V, P-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	5
10	Characteristics	7
11	Test information	10
12	Package outline	11
13	Soldering	11
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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16/16

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